

## AMENDMENTS TO THE CLAIMS

### **Claims 1-7 (Cancelled)**

**Claim 8 (Currently Amended)** A process for forming a patterned resist layer which comprises:

a) coating a substrate with a positive-working chemical-amplification photoresist composition which ~~comprises, as a uniform solution in an organic solvent~~ consists essentially of:

(A) 100 parts by weight of a film-forming resinous compound having acid-dissociable solubility-reducing groups in the molecule and capable of being imparted with an increased solubility in an aqueous alkaline solution by ~~interaction~~ interacting with an acid, which resinous compound is a copolymeric resin ~~comprising monomeric units of an ester of acrylic or methacrylic acid~~ consisting of from 50 to 85% by moles of the monomeric units of hydroxystyrene, from 10 to 30% by moles of the monomeric units of styrene and from 2 to 20% by moles of the monomeric units of a tert-alkylacrylate or methacrylate;

(B) from 1 to 20 parts by weight of an acid-generating compound which is an onium salt compound having a fluoroalkylsulfonate as the anionic constituent;

(C) from 0.01 to 5 parts by weight of a phosphorus-containing oxo acid, ~~and~~

(D) an amine selected from the group consisting of secondary amines and tertiary amines, in an amount sufficient to exhibit a quenching effect, and

(E) an organic solvent to dissolve components (A) to (D)

b) drying the coated substrate to form a photoresist layer, and

c) patternwise exposing the photoresist layer to actinic rays to form said patterned resist layer.

**Claim 9 (Currently Amended).** The process according to claim 8 wherein said actinic rays are from a KrF excimer laser beam of 248 nm. [[.]]

**Claim 10 (Original)** The process according to claim 8 wherein said actinic rays are X-rays.

**Claim 11 (Original).** The process according to claim 8 wherein said actinic rays are electron beams.

**Claim 12 (Original)** The process according to claim 8 wherein the substrate is a semiconductor wafer.

**Claim 13 (Original)** The process according to claim 12 wherein the semiconductor wafer comprises silicon.

**Claim 14 (Original)** The process according to claim 12 wherein the substrate to be coated has an undercoating film containing nitrogen or containing phosphorus and/or boron.

**Claim 15 (Original)** The process according to claim 14 wherein the undercoating film comprises at least one nitrogen-containing material which is SiN, Si<sub>3</sub>N<sub>4</sub>, SiON or TiN.

**Claim 16 (Original)** The process according to claim 14 wherein the undercoating comprises at least one phosphorus and/or boron material which is phosphosilicate glass, borosilicate glass or borophosphosilicate glass.

**Claim 17 (Original)** The process according to claim 8 wherein the phosphorus-containing oxo acid as the component (C) is selected from the group consisting of phosphoric acid, phosphorous acid, phosphonic acid, phosphinic acid, phenylphosphinic acid and phenylphosphonic acid.

**Claim 18 (Cancelled)**

**Claim 19 (Cancelled)**

**Claim 20 (Currently Amended)** The process according to claim ~~19~~ 8, wherein the tert-alkyl acrylate or methacrylate is tert-butyl acrylate or methacrylate.

**Claim 21 (Original)** The process according to claim 8 wherein the amount of the phosphorus-containing oxo acid as the component (C) is in the range from 0.1 to 2.0 parts by weight per 100 parts by weight of the component (A).

**Claim 22 (Original).** The process according to claim 8 wherein the amine is triethylamine, tributylamine, dibutylamine or triethanolamine.